

10/728132

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	224	EPROM and floating and gate and control and source and drain and region and dop\$ and n-type and p-type and polysilicon and (tunnel adj oxide) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:06
L2	58	EPROM and floating and gate and control and source and drain and region and dop\$ and n-type and p-type and polysilicon and (tunnel adj oxide) and electrode and conductivity and trench and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:07
L3	0	EPROM and floating and gate and control and source and drain and region and dop\$ and n-type and p-type and polysilicon and (tunnel adj oxide) and electrode and conductivity and trench and transistor and (partially adj2 second adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:08
L4	3	EPROM and floating and gate and control and source and drain and region and dop\$ and n-type and p-type and polysilicon and (tunnel adj oxide) and electrode and conductivity and trench and transistor and (crystallographic adj orientation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:12
L5	1	("6836001").PN.	USPAT	OR	OFF	2005/09/22 13:12